

Symbol Test Conditions

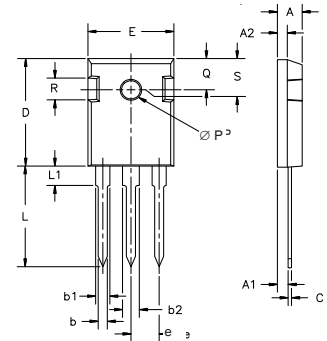
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 30\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	28	46	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3980	pF
C_{oes}			190	pF
C_{res}			45	pF
Q_g	$I_C = 40\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		115	nC
Q_{ge}			21	nC
Q_{gc}			40	nC
$t_{d(on)}$	Inductive Load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		22	ns
t_{ri}			26	ns
E_{on}			0.45	mJ
$t_{d(off)}$			130	ns
t_{fi}			116	ns
E_{off}			0.66	mJ
$t_{d(on)}$	Inductive Load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 480\text{V}, R_G = 5\Omega$ Note 2		22	ns
t_{ri}			26	ns
E_{on}			0.50	mJ
$t_{d(off)}$			190	ns
t_{fi}			157	ns
E_{off}			1.30	mJ
R_{thJC}			0.42	$^\circ\text{C/W}$
R_{thCS}			0.21	$^\circ\text{C/W}$

TO-247 (IXGH) Outline



Dim.	Millimeter	Inches
	Min. Max.	Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L1	4.50	.177
ØP	3.55 3.65	.140 .144
Q	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

Reverse Diode (SiC)

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

V_F	$I_F = 20\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$	1.65	2.10	V
	$T_J = 125^\circ\text{C}$	1.80		V
R_{thJC}			0.90	$^\circ\text{C/W}$

Notes

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (Clamp), T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

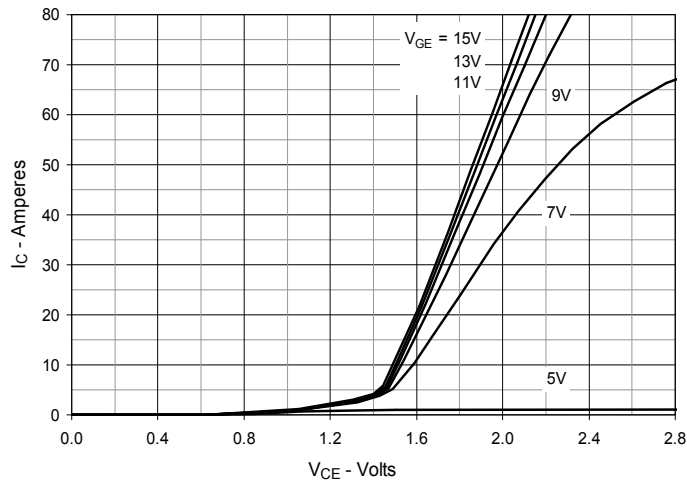


Fig. 2. Extended Output Characteristics
@ 25°C

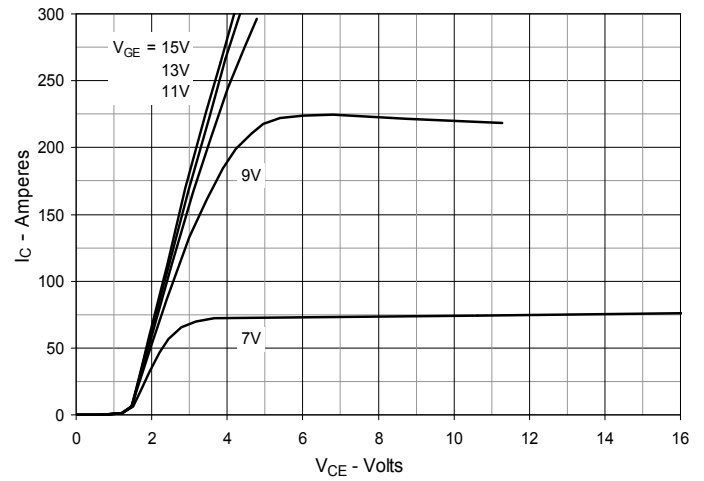


Fig. 3. Output Characteristics
@ 125°C

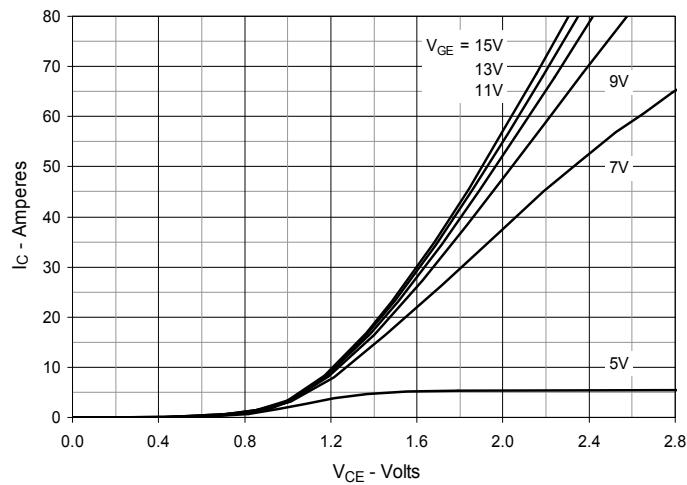


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

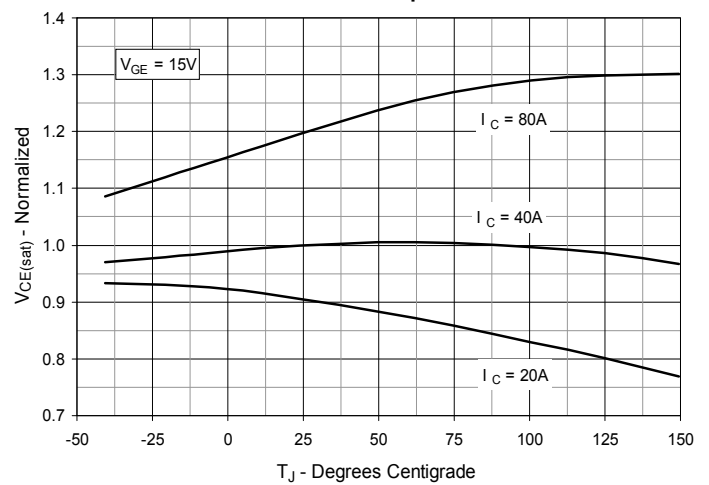


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

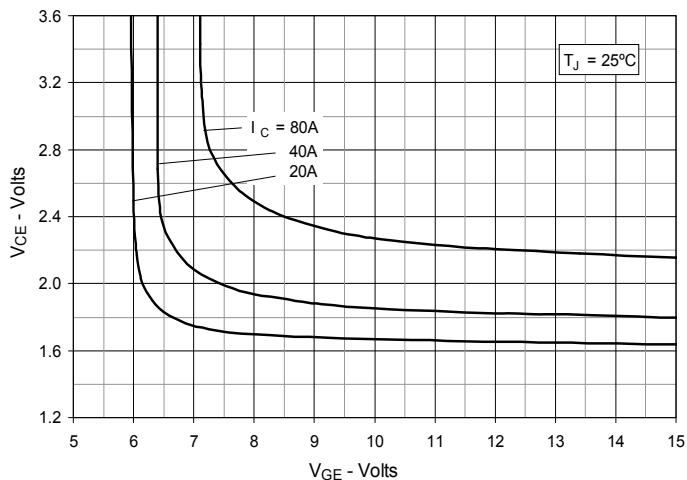


Fig. 6. Input Admittance

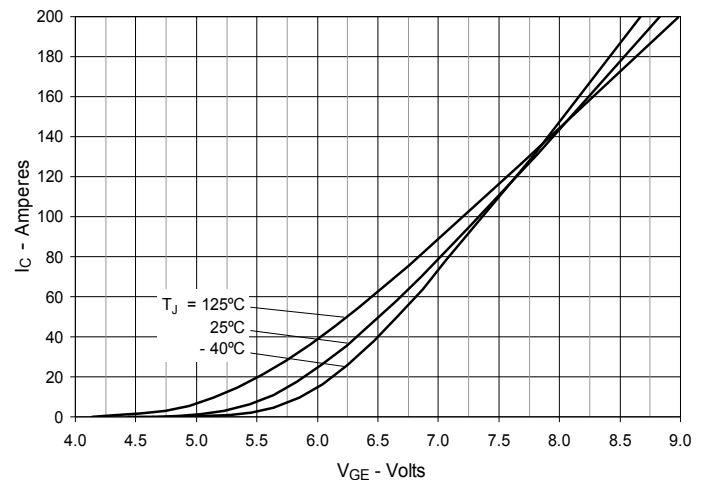


Fig. 7. Transconductance

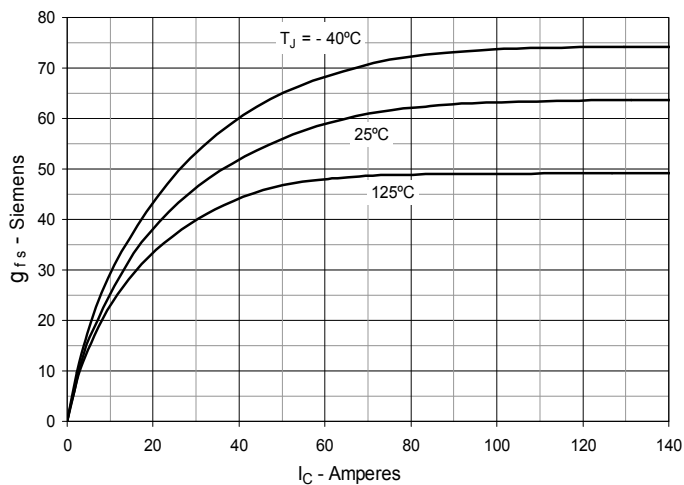


Fig. 8. Gate Charge

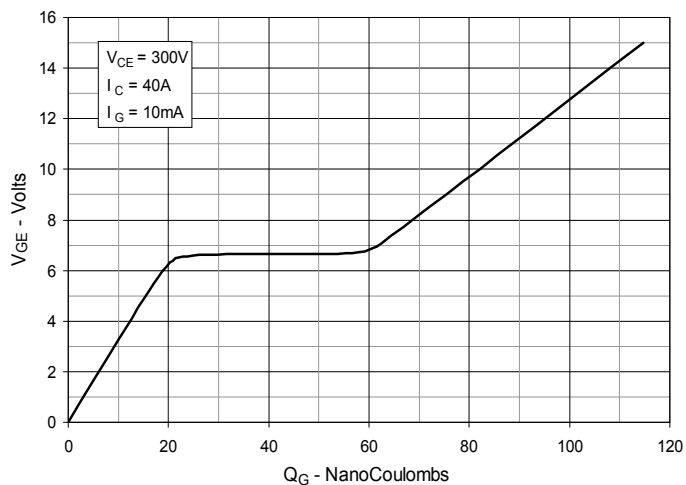


Fig. 9. Capacitance

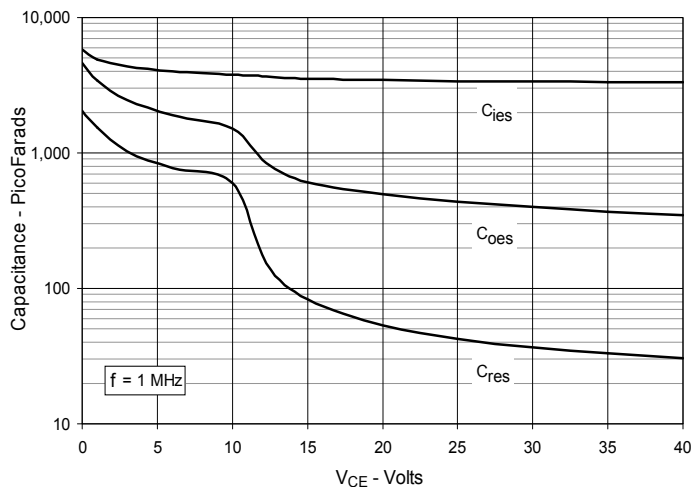


Fig. 10. Reverse-Bias Safe Operating Area

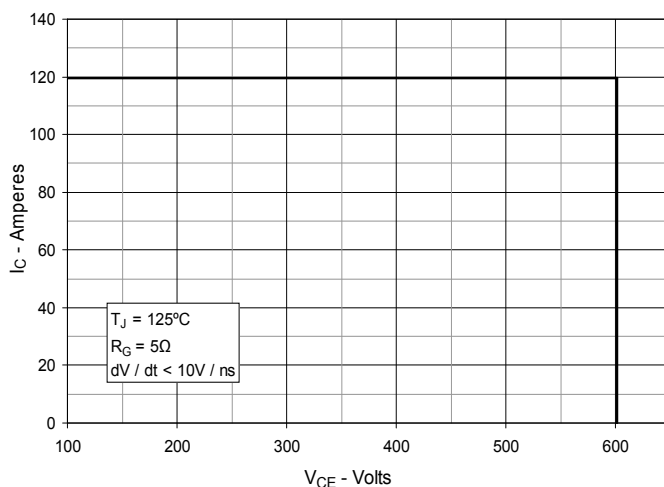
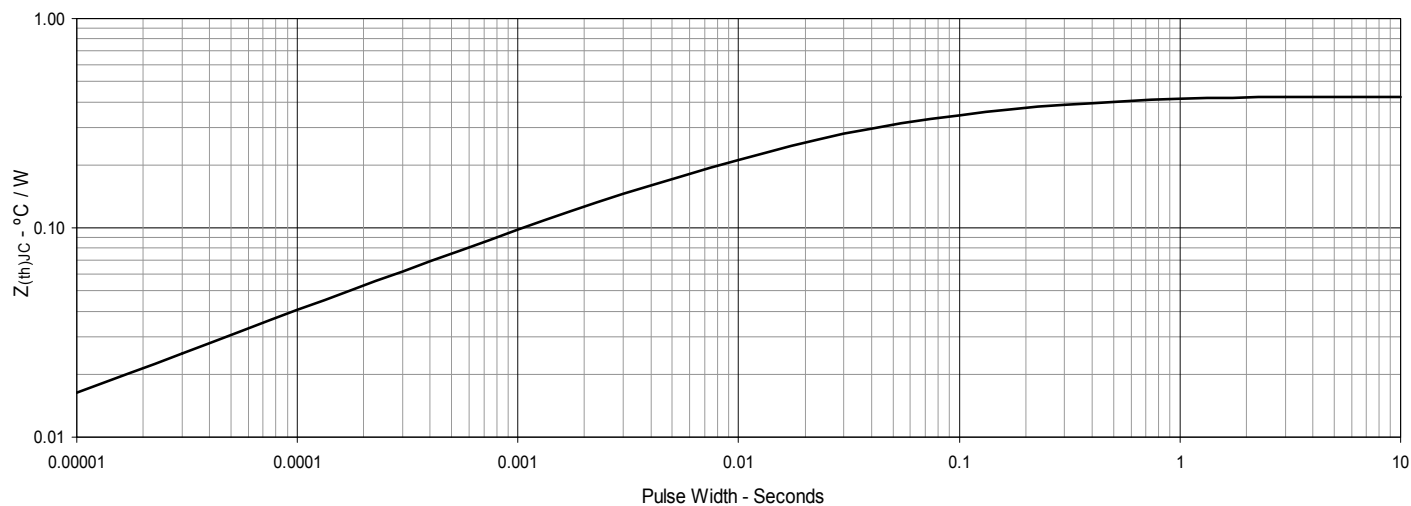
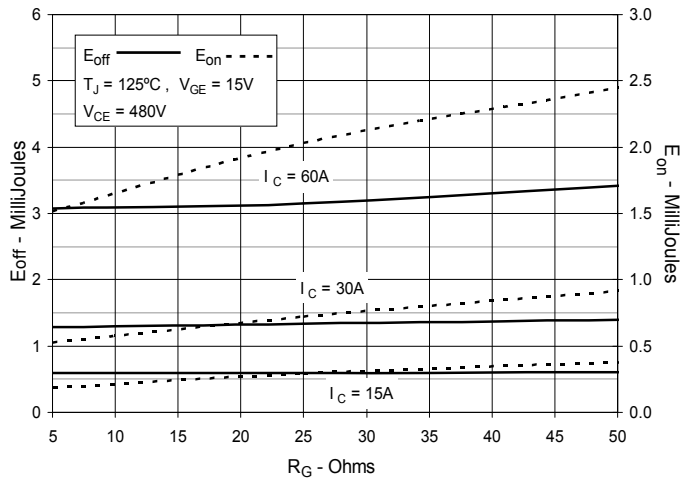


Fig. 11. Maximum Transient Thermal Impedance for IGBT

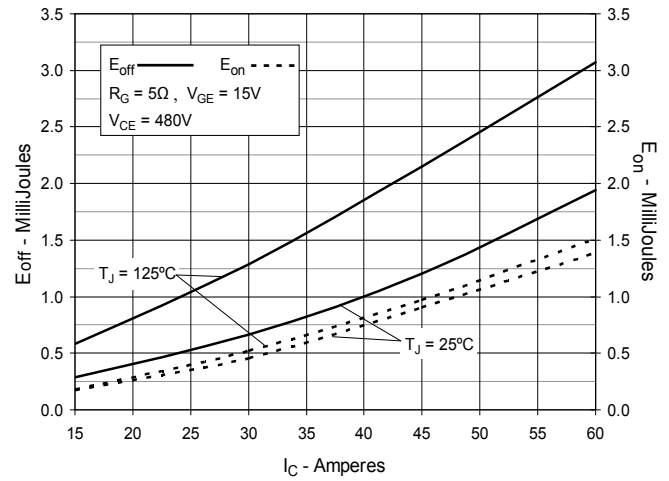


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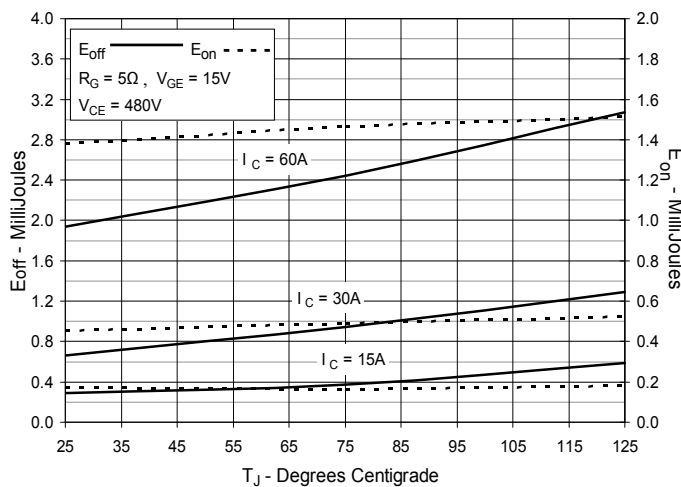
**Fig. 12. Inductive Switching
Energy Loss vs. Gate Resistance**



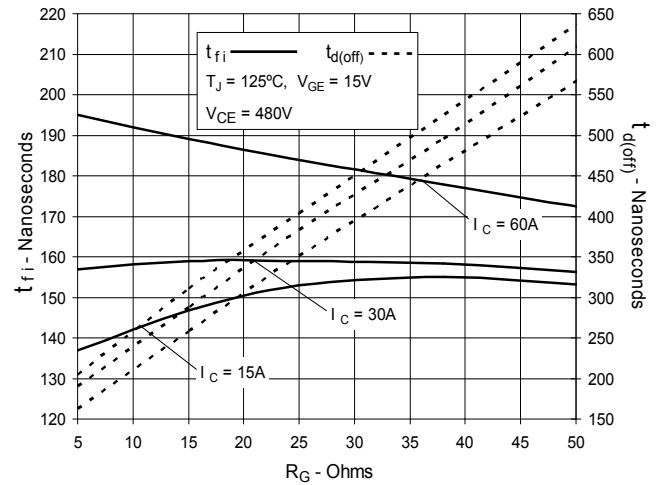
**Fig. 13. Inductive Switching
Energy Loss vs. Collector Current**



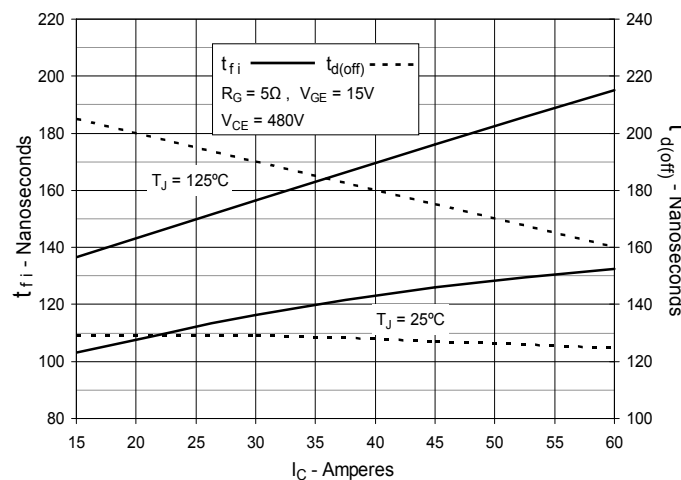
**Fig. 14. Inductive Switching
Energy Loss vs. Junction Temperature**



**Fig. 15. Inductive Turn-off
Switching Times vs. Gate Resistance**



**Fig. 16. Inductive Turn-off
Switching Times vs. Collector Current**



**Fig. 17. Inductive Turn-off
Switching Times vs. Junction Temperature**

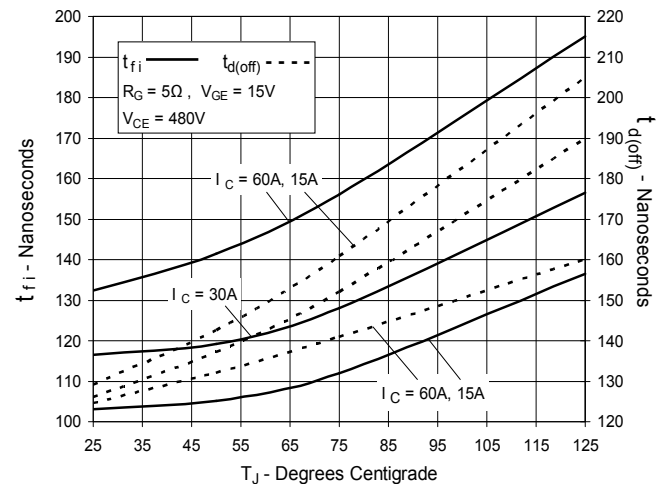


Fig. 18. Inductive Turn-on
Switching Times vs. Gate Resistance

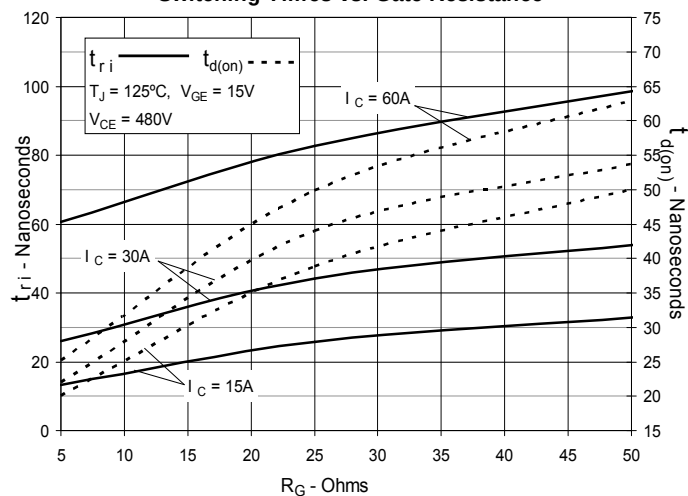


Fig. 19. Inductive Turn-on
Switching Times vs. Collector Current

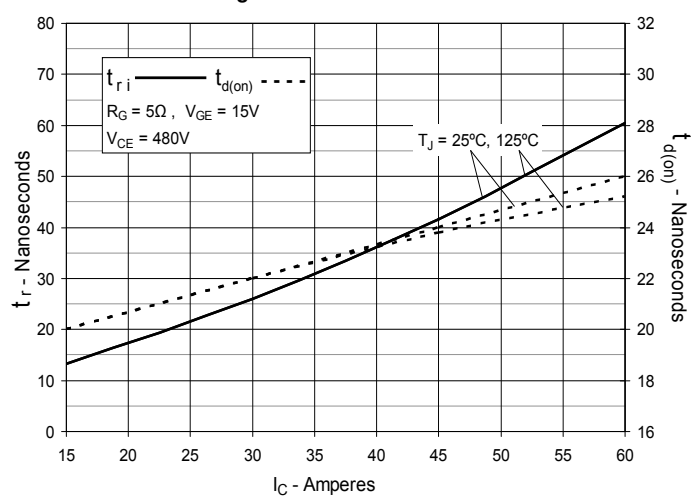


Fig. 20. Inductive Turn-on
Switching Times vs. Junction Temperature

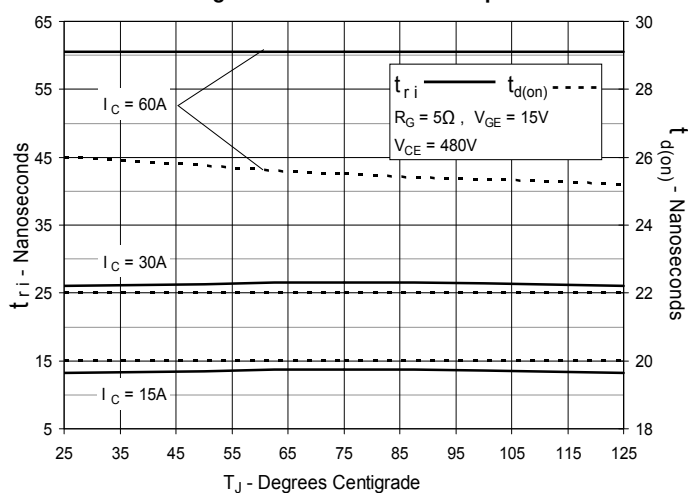


Fig. 21. Forward Current vs. Forward Voltage

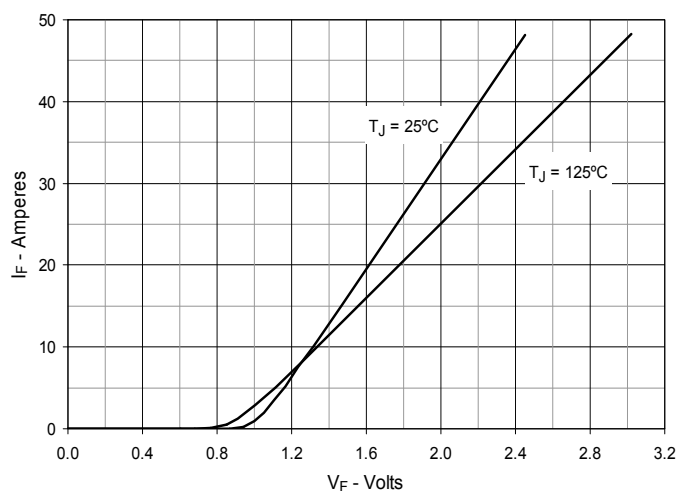
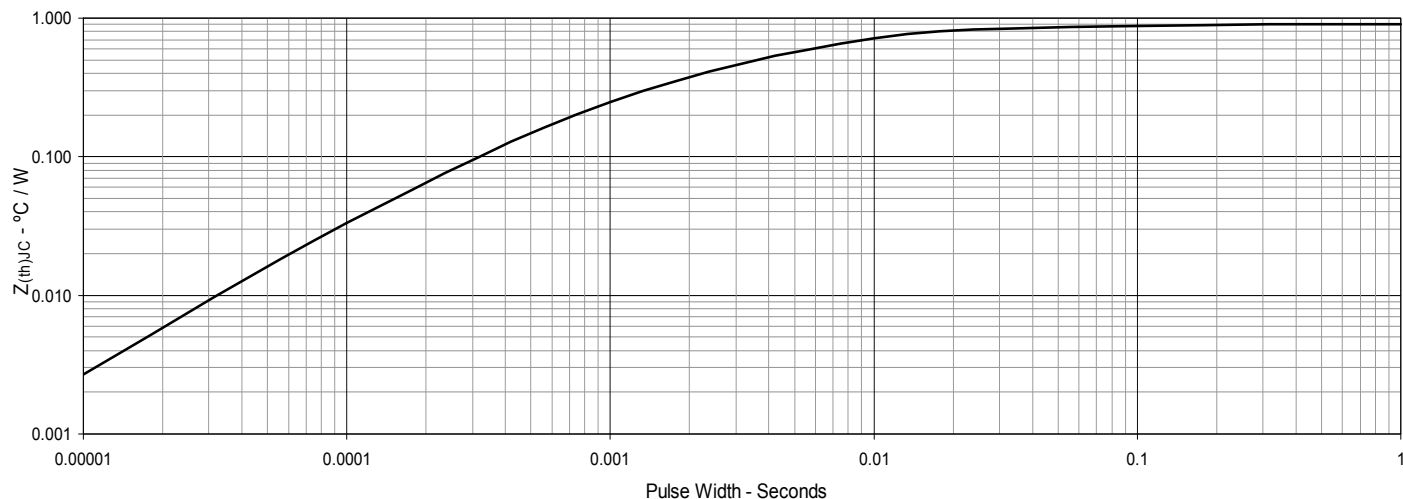


Fig. 22. Maximum Transient Thermal Impedance for Diodes



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